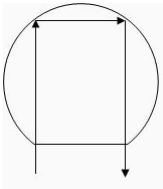


Part Number	Customer
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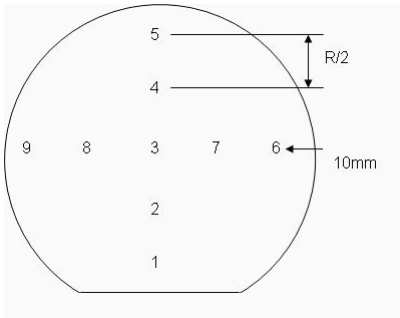
Category		Parameter	Specification	Measurement Method
Overall	Wafer	1.0 Diameter	150.00 +/- 0.20 mm	
		2.0 Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
		3.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
		4.0 Secondary Flat Orientation	none or SEMI Standard	Wafer Vendor
		5.0 Overall Thickness	500.00 +/- 100.00 μm	ADE, 100%
		6.0 Total Thickness Variation (TTV)	<10.00μm	Guaranteed by Process
		7.0 Bow	40.00 +/- 0.00 μm	ADE to ASTM F534, 20%
		8.0 Warp	40.00 +/- 0.00 μm	ADE to ASTM F657, 20%
		9.0 Edge Chips	0	Bright Light, 100%
		10.0 Edge Exclusion	5mm	
Handle	Silicon	11.0 Handle Growth Method	CZ	Wafer Vendor
		12.0 Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
		13.0 Handle Thickness	500.00 +/- 100.00 μm	ADE, 100%
		14.0 Handle Doping Type	Any	Wafer Vendor
		15.0 Handle Dopant	Any	Wafer Vendor
		16.0 Handle Resistivity	0.001 - 0.01 Ohm cm	Wafer Vendor
		17.0 Backside Finish	Polished with lasermark, chuck marks and handling per additional comments.	Guaranteed by process

Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information